

HIGH POWER DIODE

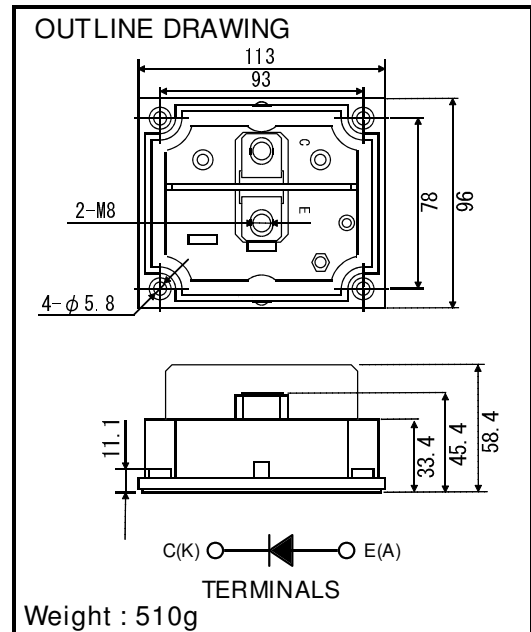
HITACHI



MDN1200D33

Spec.No.SR2-SP-03010 R1

Unit in mm



FEATURES

- Low noise due to soft and fast recovery diodes
- High reliability, high durability diodes
- Isolated heatsink (Terminals to base)
- High thermal fatigue durability
($\Delta T_c=70K$, $N>30000$ cycles)

MAXIMUM ALLOWABLE RATINGS ($T_c = 25\text{degC}$)

Items		Type		MDN1200D33
Repetitive Peak Reverse Voltage		V_{RRM}	V	3,300
Forward Current	DC	I_F	A	1,200
	1ms	I_{FM}	A	2,400
Junction Temperature		T_j	degC	-40 ~ +125
Storage Temperature		T_{stg}	degC	-40 ~ +125
Isolation Voltage		-	$V_{(RMS)}$	5,400(AC 1 minute)
Screw Torque	Terminals (M8)	-	N·m	7.4+/-0.5
	Mounting (M5)	-	N·m	2.6+/-0.2

CHARACTERISTICS ($T_c = 25 \text{ degC}$)

Items	Symbols	Units	Min.	Typ.	Max.	Test Condition
Repetitive Reverse Current	I_{RRM}	mA	—	—	4.0	$V_R=3300V$
Forward Voltage Drop	V_F	V	—	3.2	4.2	$I_F=1200A$
Reverse Recovery Time	t_{rr}	μs	—	0.8	1.4	$T_j=125\text{degC}$, $V_D=1650V$, $I_F=1200A$
Thermal Impedance	$R_{th(j-c)}$	K/W	—	—	0.017	Junction to case
	$R_{th(c-f)}$	K/W	—	0.016	—	Case to fin

* Please contact our representatives at order.

* For improvement, specifications are subject to change without notice.

* Remarks : For actual application, please confirm this spec sheet is the newest revision.

HITACHI POWER SEMICONDUCTORS

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